



Si5853DDC vs. Si5853CDC

Description: P-Channel, 20-V (D-S) MOSFET with Schottky Diode

Package: 1206-8 ChipFET®

Pin Out: Identical

Part Number Replacements: Si5853DDC-T1-E3 replaces Si5853CDC-T1-E3

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted				
PARAMETER	SYMBOL	Si5853DDC	Si5853CDC	UNIT
Drain-Source Voltage	V_{DS}	- 20	- 20	V
Gate-Source Voltage	V_{GS}	± 8	± 8	
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	- 2.9	- 2.9	A
	$T_A = 70\text{ }^\circ\text{C}$	- 2.3	- 2.3	
Pulsed Drain Current	I_{DM}	- 10	- 10	
Continuous Source Current (MOSFET Diode Conduction)	I_S	- 1.1	- 1.2	
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	1.3	1.5	W
	$T_A = 70\text{ }^\circ\text{C}$	0.8	0.9	
Operating Junction and Storage Temperature Range	T_J and T_{stg}	- 55 to 150	- 55 to 150	$^\circ\text{C}$
Maximum Junction-to-Ambient	R_{thJA}	95	85	$^\circ\text{C/W}$

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted									
PARAMETER	SYMBOL	Si5853DDC			Si5853CDC			UNIT	
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Static									
Gate-Threshold Voltage	$V_{GS(th)}$	- 0.4		- 1.0	- 0.45		- 1.0	V	
Gate-Body Leakage	I_{GSS}			± 100			± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}			- 1			- 1	μA	
On-State Drain Current	$V_{GS} = - 4.5\text{ V}$	$I_{D(on)}$	- 10		- 10			A	
Drain-Source On-Resistance	$V_{GS} = - 4.5\text{ V}$	$R_{DS(on)}$		0.085	0.105		0.086	0.104	Ω
	$V_{GS} = - 2.5\text{ V}$			0.117	0.143		0.120	0.144	
	$V_{GS} = - 1.8\text{ V}$			0.155	0.188		0.170	0.205	
Forward Transconductance		g_{fs}		7		6		S	
Diode Forward Voltage		V_{SD}		- 0.85	- 1.2		- 0.8	- 1.2	V
Dynamic									
Total Gate Charge		Q_g		4.7	7.1		4.2	6.5	nC
Gate-Source Charge		Q_{gs}		0.65			0.7		
Gate-Drain Charge		Q_{gd}		1.35			1.0		
Gate Resistance		R_g		6.5			6.2		Ω

SCHOTTKY SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted								
PARAMETER	SYMBOL	Si5853DDC			Si5853CDC			UNIT
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Forward Voltage Drop	V_F		0.468	0.560		0.468	0.560	V
Maximum Reverse Leakage Current	I_{rm}		0.0081	0.080		0.0081	0.080	mA
Junction Capacitance	C_T		30			30		pF

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.